Microsemi
POWER PRODUCTS GROUP

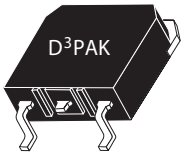
Power MOS 8 Cooler!

APT4F120S

1200V, 4A, 4.2Ω Max Trr ≤195nS

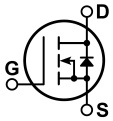
N-Channel FREDFET

Power MOS 8™ is a high speed, high voltage N-channel switch-mode power MOSFET. This 'FREDFET' version has a drain-source (body) diode that has been optimized for high reliability in ZVS phase shifted bridge and other circuits through reduced t_{rr}, soft recovery, and high recovery dv/dt capability. Low gate charge, high gain, and a greatly reduced ratio of C_{rss}/C_{iss} result in excellent noise immunity and low switching loss. The intrinsic gate resistance and capacitance of the poly-silicon gate structure help control di/dt during switching, resulting in low EMI and reliable paralleling, even when switching at very high frequency.



APT4F120S

Single die FREDFET



FEATURES

- **Fast switching with low EMI**
- **Low t_{rr} for high reliability**
- **Ultra low C_{rss} for improved noise immunity**
- **Low gate charge**
- **Avalanche energy rated**
- **RoHS compliant**

TYPICAL APPLICATIONS

- **ZVS phase shifted and other full bridge**
- **Half bridge**
- **PFC and other boost converter**
- **Buck converter**
- **Single and two switch forward**
- **Flyback**

Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
I_D	Continuous Drain Current @ T_C = 25°C	4	A
	Continuous Drain Current @ T_C = 100°C	3	
I_{DM}	Pulsed Drain Current①	15	
V_{GS}	Gate - Source Voltage	±30	V
E_{AS}	Single Pulse Avalanche Energy②	310	mJ
I_{AR}	Avalanche Current, Repetitive or Non-Repetitive	2	A

Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Max
P_D	Total Power Dissipation @ T_C = 25°C	-	-	175	W
$R_{\theta JC}$	Junction to Case Thermal Resistance	-	-	0.7	°C/W
$R_{\theta CS}$	Case to Sink Thermal Resistance, Flat, Greased Surface	-	.11	-	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55	-	-	°C
W_T	Package Weight	-	0.14	-	oz
		-	3.95	-	g

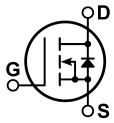
Static Characteristics T_J = 25°C unless otherwise specified **APT4F120S**

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
$V_{BR(DSS)}$	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250µA		1200			V
$\Delta V_{BR(DSS)}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I_D = 250µA			1.41		V/°C
$R_{DS(on)}$	Drain-Source On Resistance ③	V_{GS} = 10V, I_D = 2A			3.42	4.2	Ω
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 0.5mA		2.5	4	5	V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold Voltage Temperature Coefficient				-10		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 1200V, V_{GS} = 0V	T_J = 25°C			250	µA
			T_J = 125°C			1000	
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±30V				±100	nA

Dynamic Characteristics T_J = 25°C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
g_{fs}	Forward Transconductance	V_{DS} = 50V, I_D = 2A		4.5		S
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 25V f = 1MHz		1385		pF
C_{rss}	Reverse Transfer Capacitance			17		
C_{oss}	Output Capacitance			100		
$C_{o(cr)}$ ④	Effective Output Capacitance, Charge Related	V_{GS} = 0V, V_{DS} = 0V to 800V		40		
$C_{o(er)}$ ⑤	Effective Output Capacitance, Energy Related			20		
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, I_D = 2A, V_{DS} = 600V		43		nC
Q_{gs}	Gate-Source Charge			7		
Q_{gd}	Gate-Drain Charge			20		
$t_{d(on)}$	Turn-On Delay Time	**Resistive Switching** V_{DD} = 800V, I_D = 2A R_G = 10Ω ⑥, V_{GG} = 15V		7.4		ns
t_r	Current Rise Time			4.4		
$t_{d(off)}$	Turn-Off Delay Time			24		
t_f	Current Fall Time			6.9		

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
I_S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode (body diode) 				4	A
I_{SM}	Pulsed Source Current (Body Diode) ①					15	
V_{SD}	Diode Forward Voltage	I_{SD} = 2A, T_J = 25°C, V_{GS} = 0V			0.8	1.2	V
t_{rr}	Reverse Recovery Time	I_{SD} = 2A③, di_{SD}/dt = 100A/µs, V_{DD} = 100V	T_J = 25°C		170	195	nS
			T_J = 125°C		330	400	
Q_{rr}	Reverse Recovery Charge		T_J = 25°C		.510		µC
			T_J = 125°C		1.0		
I_{rrm}	Reverse Recovery Current		T_J = 25°C		6.0		A
			T_J = 125°C		8.3		
dv/dt	Peak Recovery dv/dt	I_{SD} ≤ 2A, di/dt≤1000Aµs, V_{DD} = 800V, T_J = 125°C				20	V/ns

① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.
② Starting at T_J = 25°C, L = 155.0mH, R_G = 25Ω, I_{AS} = 2A.
③ Pulse test: Pulse Width < 380µs, duty cycle < 2%.
④ $C_{o(cr)}$ is defined as a fixed capacitance with the same stored charge as C_{OSS} with V_{DS} = 67% of $V_{(BR)DSS}$.
⑤ $C_{o(er)}$ is defined as a fixed capacitance with the same stored energy as C_{OSS} with V_{DS} = 67% of $V_{(BR)DSS}$. To calculate $C_{o(er)}$ for any value of V_{DS} less than $V_{(BR)DSS}$, use this equation: $C_{o(er)}$ = -8.32E-8/V_{DS}^2 + 3.49E-8/V_{DS} + 1.30E-10.
⑥ R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

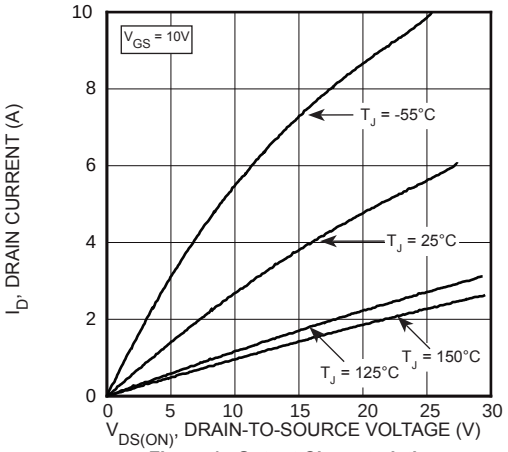


Figure 1, Output Characteristics

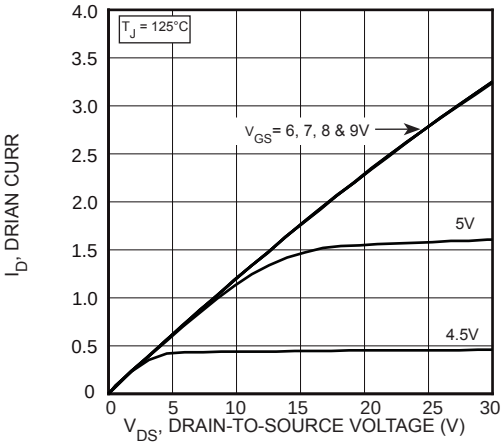


Figure 2, Output Characteristics

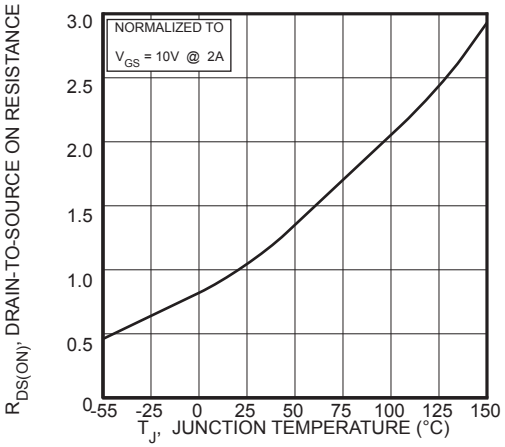


Figure 3, $R_{DS(ON)}$ vs Junction Temperature

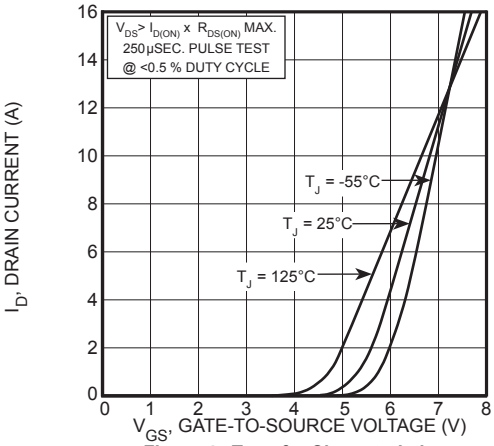


Figure 4, Transfer Characteristics

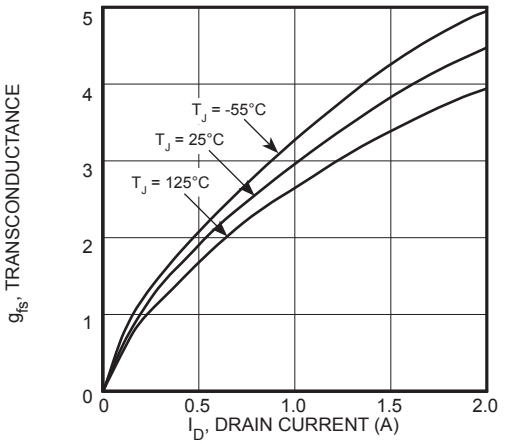


Figure 5, Gain vs Drain Current

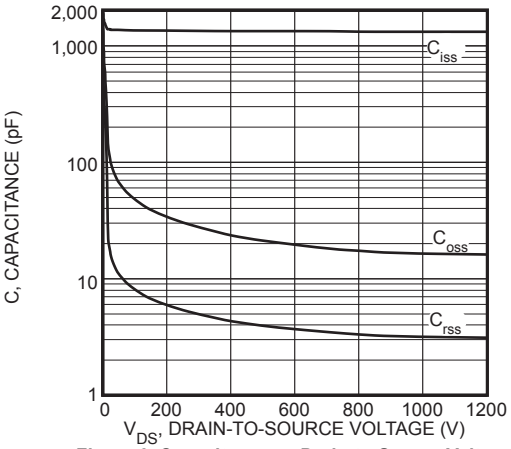


Figure 6, Capacitance vs Drain-to-Source Voltage

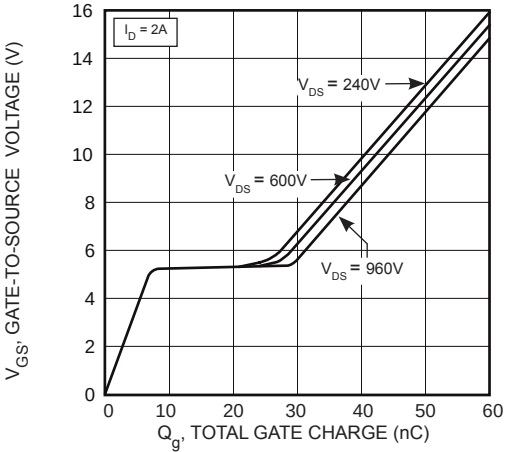


Figure 7, Gate Charge vs Gate-to-Source Voltage

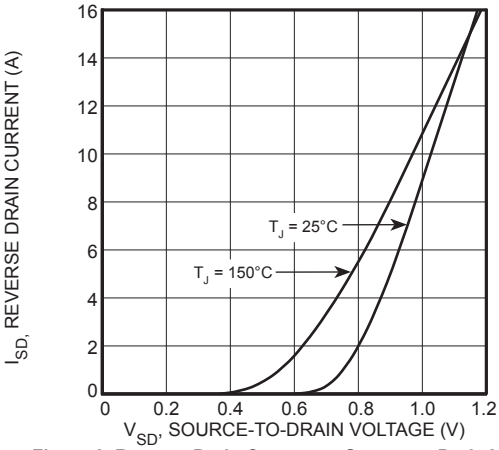


Figure 8, Reverse Drain Current vs Source-to-Drain Voltage

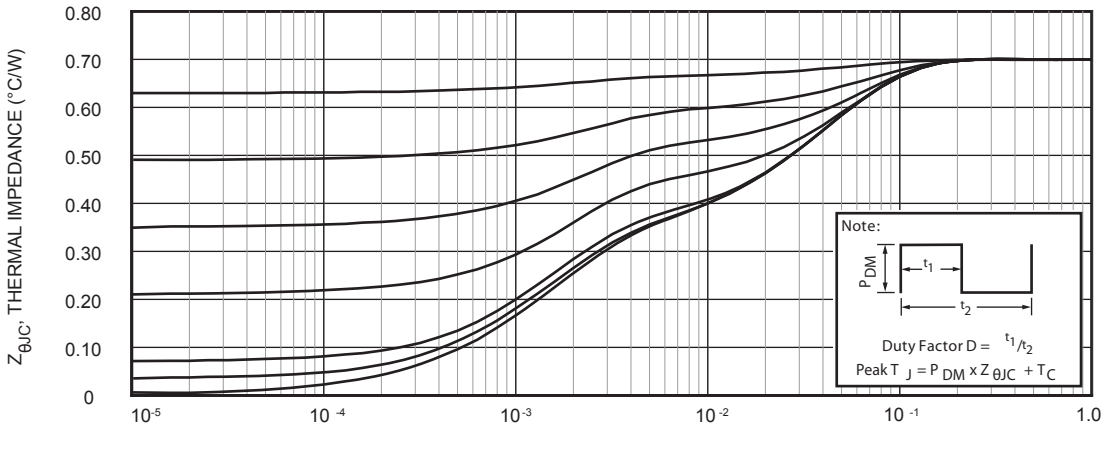
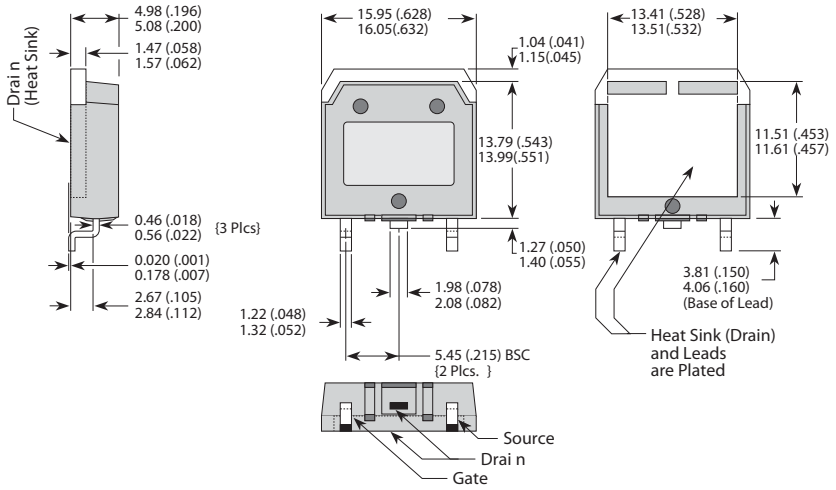


FIGURE 9. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

D³PAK Package Outline

e3 100% Sn Plated



Dimensions in Millimeters (Inches)